



PATENT
Docket No.: 8733.126.00

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Duck-Kyun Choi

Application No.: 09/170,625

Group Art Unit: 2823

Filed: October 13, 1998

Examiner: G. Fourson

For: A METHOD FOR FABRICATING A THIN
FILM TRANSISTOR

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AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In response to Granting a Request to Restart Period for Response to April 19, 2002, and the period for response being extended by the attached Petition For Extension of Time for three months, Applicant requests that the application be amended as follows:

IN THE CLAIMS:

Please amend claims 1 and 14 as follows (A marked-up version of the amended claims is attached):

1. (Twice Amended) A method of fabricating a thin film transistor for a liquid crystal display having a plurality of pixels comprising:

- forming an amorphous silicon layer as an active layer on a glass substrate;
- forming a gate insulating layer and a gate electrode on the amorphous silicon layer;
- doping impurities of a first conductive type in the amorphous silicon layer;
- forming a metal layer on exposed portions of the amorphous silicon layer; and

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